

WHAT IS CLAIMED IS:

1. A transistor, comprising:
at least a monocrystalline semiconductor layer and a gate insulating film provided on the monocrystalline semiconductor layer,
the gate insulating film having a thermal oxide film formed on the monocrystalline semiconductor layer and at least one vapor-deposited insulating film formed on the thermal oxide film.
2. The transistor according to claim 1, the monocrystalline semiconductor layer being made of monocrystalline silicon.
3. The transistor according to claim 1, the monocrystalline semiconductor layer being a mesa type.
4. The transistor according to claim 1, the monocrystalline semiconductor layer having a thickness of 15 to 60 nm.
5. The transistor according to claim 1, the thermal oxide film of the gate insulating film having a thickness of 5 to 50 nm.
6. A method of manufacturing a transistor in which a channel region and source and drain regions are formed in a monocrystalline semiconductor layer and a gate electrode is formed on the monocrystalline semiconductor layer with a gate insulating film therebetween, the method comprising:
forming the gate insulating film including at least thermally oxidizing the monocrystalline semiconductor layer to form a thermal oxide film on a surface of the monocrystalline semiconductor layer; and
forming a vapor-deposited insulating film on the thermal oxide film using a vapor deposition method.
7. The method of manufacturing a transistor according to claim 6, thermally oxidizing the monocrystalline semiconductor layer to form the thermal oxide film on the surface of the monocrystalline semiconductor layer being carried out by using both a dry thermal oxidation process and a wet thermal oxidation process.
8. An electro-optical device, comprising:
a transistor according to claim 1.
9. An electro-optical device in which an electro-optical material is interposed between a pair of substrates facing each other,
a transistor according to claim 1 being provided as a switching element in a display area.

10. A semiconductor device, comprising:
a transistor according to claim 1.
11. An electronic apparatus, comprising:
an electro-optical device according to claim 8.
12. An electro-optical device, comprising:
a transistor obtained by the manufacturing method of claim 6.
13. An electro-optical device in which an electro-optical material is interposed
between a pair of substrates facing each other, a transistor obtained by the manufacturing
method according to claim 6 being provided as a switching element in a display area.
14. A semiconductor device, comprising:
a transistor obtained by the manufacturing method according to claim 6.
15. An electronic apparatus, comprising:
a semiconductor device according to claim 10.